

### ABSTRACT OF THE DISCLOSURE

A compound semiconductor switching device is based on a designing guideline that isolation should be assured by reducing the gate width of switching FET, thereby  
5 reducing the capacitance of the FET. Proper isolation between the two signal passes IS obtained with a FET gate width of about  $700 \mu\text{m}$  or smaller at a signal frequency of about 2.4 GHz or higher, without employing a shunt FET.

1.051510-0E055860